

# XN0A311 (XN1A311)

Silicon NPN epitaxial planar transistor (Tr1)  
 Silicon PNP epitaxial planar transistor (Tr2)

For switching/digital circuits

**■ Features**

- Two elements incorporated into one package  
 (Transistors with built-in resistor)
- Reduction of the mounting area and assembly cost by one half

**■ Basic Part Number of Element**

- UNR1211 (UN1211) + UNR1111 (UN1111)

**■ Absolute Maximum Ratings  $T_a = 25^\circ\text{C}$**

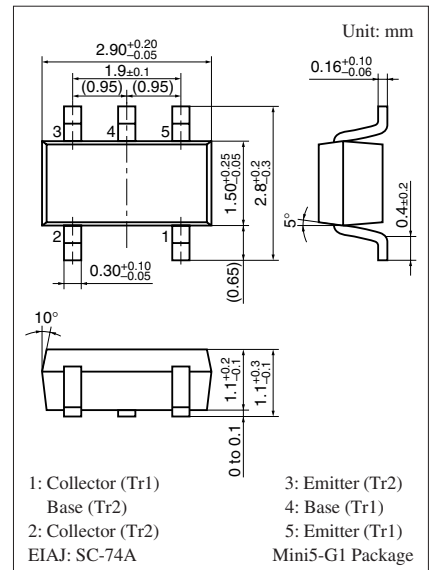
Parameter		Symbol	Rating	Unit
Tr1	Collector to base voltage	$V_{CBO}$	50	V
	Collector to emitter voltage	$V_{CEO}$	50	V
	Collector current	$I_C$	100	mA
Tr2	Collector to base voltage	$V_{CBO}$	-50	V
	Collector to emitter voltage	$V_{CEO}$	-50	V
	Collector current	$I_C$	-100	mA
Overall	Total power dissipation	$P_T$	300	mW
	Junction temperature	$T_j$	150	$^\circ\text{C}$
	Storage temperature	$T_{stg}$	-55 to +150	$^\circ\text{C}$

**■ Electrical Characteristics  $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$**

- Tr1

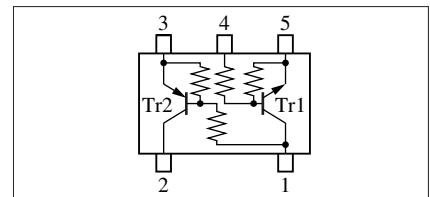
Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector to base voltage	$V_{CBO}$	$I_C = 10 \mu\text{A}, I_E = 0$	50			V
Collector to emitter voltage	$V_{CEO}$	$I_C = 2 \text{ mA}, I_B = 0$	50			V
Collector cutoff current	$I_{CBO}$	$V_{CB} = 50 \text{ V}, I_E = 0$			0.1	$\mu\text{A}$
	$I_{CEO}$	$V_{CE} = 50 \text{ V}, I_B = 0$			0.5	
Emitter cutoff current	$I_{EBO}$	$V_{EB} = 6 \text{ V}, I_C = 0$			0.5	mA
Forward current transfer ratio	$h_{FE}$	$V_{CE} = 10 \text{ V}, I_C = 5 \text{ mA}$	35			
Collector to emitter saturation voltage	$V_{CE(sat)}$	$I_C = 10 \text{ mA}, I_B = 0.3 \text{ mA}$			0.25	V
High-level output voltage	$V_{OH}$	$V_{CC} = 5 \text{ V}, V_B = 0.5 \text{ V}, R_L = 1 \text{ k}\Omega$	4.9			V
Low-level output voltage	$V_{OL}$	$V_{CC} = 5 \text{ V}, V_B = 2.5 \text{ V}, R_L = 1 \text{ k}\Omega$			0.2	V
Input resistance	$R_1$		-30%	10	+30%	$\text{k}\Omega$
Resistance ratio	$R_1/R_2$		0.8	1.0	1.2	
Gain bandwidth product	$f_T$	$V_{CB} = 10 \text{ V}, I_E = -2 \text{ mA}, f = 200 \text{ MHz}$		150		MHz

(Note) The part number in the parenthesis shows conventional part number.



Marking Symbol: FN

Internal Connection

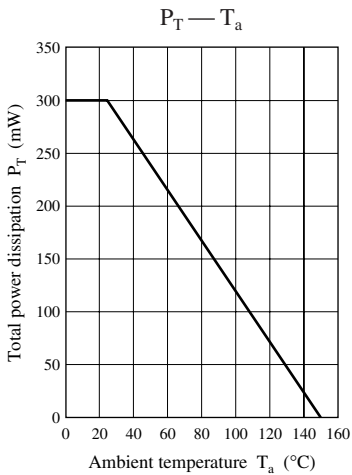


■ Electrical Characteristics (continued)  $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

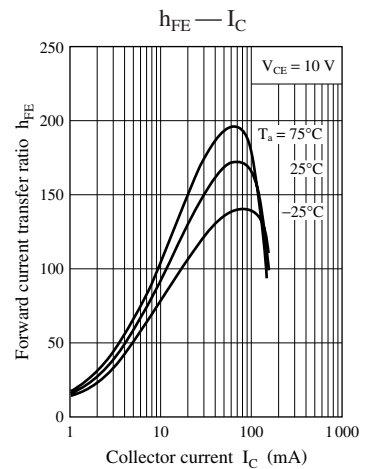
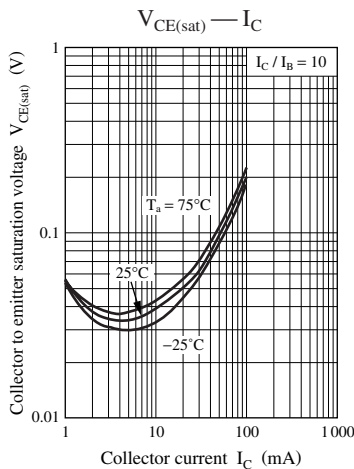
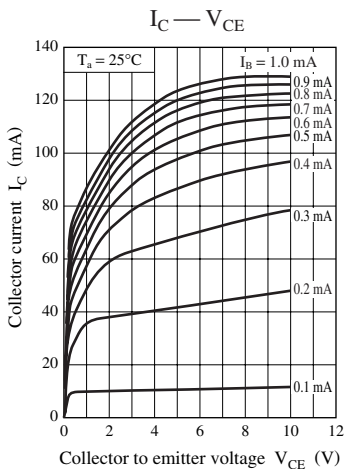
• Tr2

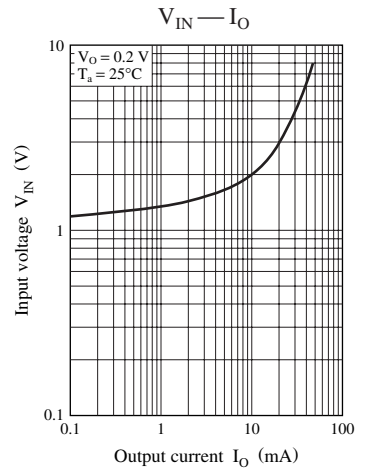
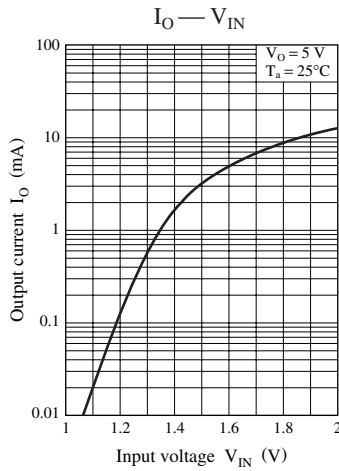
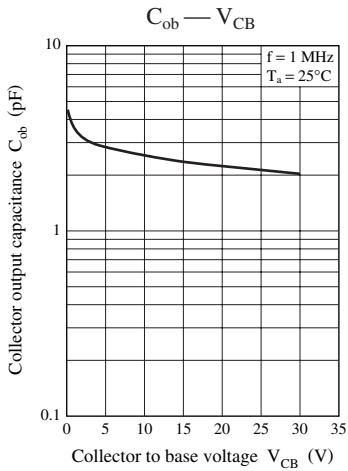
Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector to base voltage	$V_{CBO}$	$I_C = -10 \mu\text{A}, I_E = 0$	-50			V
Collector to emitter voltage	$V_{CEO}$	$I_C = -2 \text{ mA}, I_B = 0$	-50			V
Collector cutoff current	$I_{CBO}$	$V_{CB} = -50 \text{ V}, I_E = 0$			-0.1	$\mu\text{A}$
	$I_{CEO}$	$V_{CE} = -50 \text{ V}, I_B = 0$			-0.5	$\mu\text{A}$
Emitter cutoff current	$I_{EBO}$	$V_{EB} = -6 \text{ V}, I_C = 0$			-0.5	mA
Forward current transfer ratio	$h_{FE}$	$V_{CE} = -10 \text{ V}, I_C = -5 \text{ mA}$	35			
Collector to emitter saturation voltage	$V_{CE(sat)}$	$I_C = -10 \text{ mA}, I_B = -0.3 \text{ mA}$			-0.25	V
High-level output voltage	$V_{OH}$	$V_{CC} = -5 \text{ V}, V_B = -0.5 \text{ V}, R_L = 1 \text{ k}\Omega$	-4.9			V
Low-level output voltage	$V_{OL}$	$V_{CC} = -5 \text{ V}, V_B = -2.5 \text{ V}, R_L = 1 \text{ k}\Omega$			-0.2	V
Input resistance	$R_1$		-30%	10	+30%	$\text{k}\Omega$
Resistance ratio	$R_1/R_2$		0.8	1.0	1.2	
Gain bandwidth product	$f_T$	$V_{CB} = -10 \text{ V}, I_E = 1 \text{ mA}, f = 200 \text{ MHz}$		80		MHz

Common characteristics chart

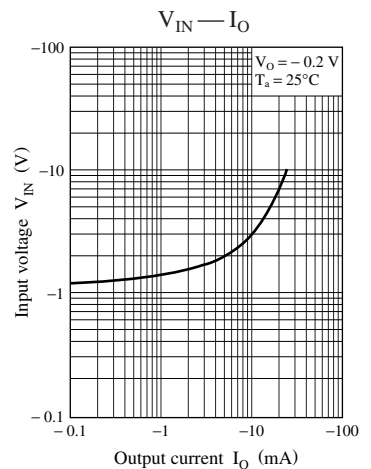
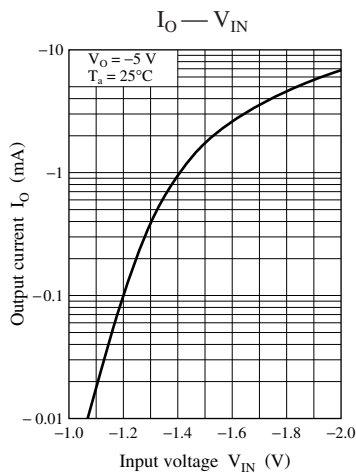
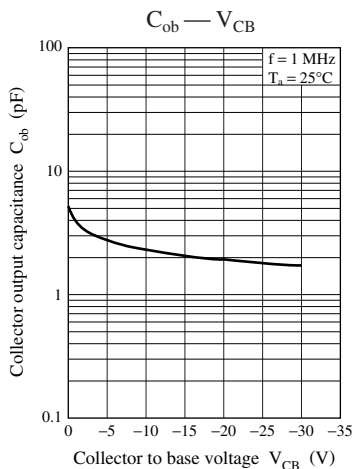
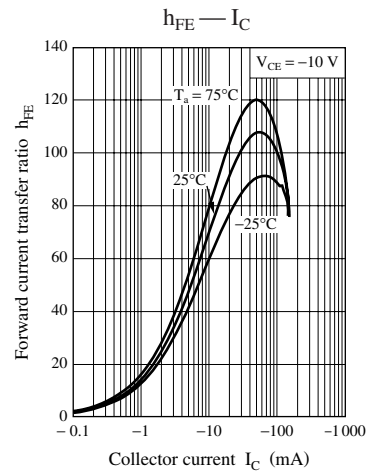
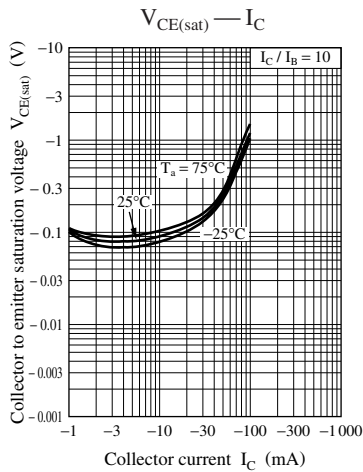
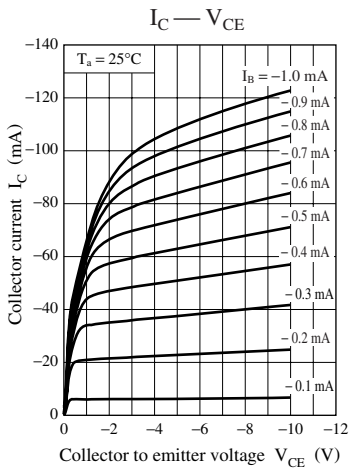


Characteristics charts of Tr1





Characteristics charts of Tr2



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